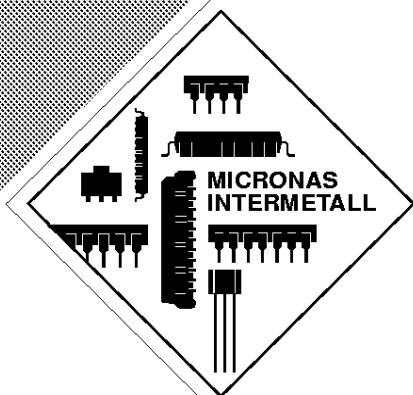




PRELIMINARY DATA SHEET

HAL400, HAL401

Linear Hall Effect Sensor ICs



Edition June 29, 1998
6251-346-4PD

 **MICRONAS**
INTERMETALL

Linear Hall Effect Sensor ICs in CMOS technology

Release Notes: Revision bars indicate significant changes to the previous edition.

Introduction

The HAL400 and HAL401 are Linear Hall Effect Sensors produced in CMOS technology. The sensors include a temperature-compensated Hall plate with choppered offset compensation, two linear output stages, and protection devices (see Fig. 2).

The output voltage is proportional to the magnetic flux density through the hall plate. The choppered offset compensation leads to stable magnetic characteristics over supply voltage and temperature.

The HAL400 and HAL401 can be used for magnetic field measurements, current measurements, and detection of any mechanical movement. Very accurate angle measurements or distance measurements can also be done. The sensor is very robust and can be used in electrical and mechanical hostile environments.

The HAL400 operates linear in the magnetic field range from -75 mT up to 75 mT.

The HAL401 operates linear in the magnetic field range from -50 mT up to 50 mT.

The sensor is designed for industrial and automotive applications and operates in the ambient temperature range from -40 °C up to 150 °C.

The HAL400 and HAL401 sensors are available in the SMD-package SOT-89A.

Features:

- switching offset compensation at 147 kHz
- low magnetic offset
- extremely sensitive
- operates from 4.8 to 12 V supply voltage
- wide temperature range $T_A = -40 \text{ }^\circ\text{C}$ to $+150 \text{ }^\circ\text{C}$
- overvoltage protection
- reverse voltage protection of V_{DD} -pin
- differential output
- accurate absolute measurements of DC and low frequency magnetic fields
- on-chip temperature compensation
- low 1/f-noise

Marking Code

Type	Temperature Range		
	A	E	C
HAL400SO	400A	400E	400C
HAL401SO	401A	401E	401C

Operating Junction Temperature Range (T_J)

A: $T_J = -40 \text{ }^\circ\text{C}$ to $+170 \text{ }^\circ\text{C}$

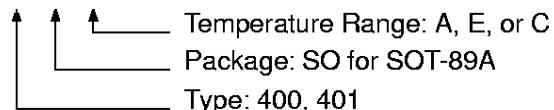
E: $T_J = -40 \text{ }^\circ\text{C}$ to $+100 \text{ }^\circ\text{C}$

C: $T_J = 0 \text{ }^\circ\text{C}$ to $+100 \text{ }^\circ\text{C}$

The relationship between ambient temperature (T_A) and junction temperature (T_J) is explained on page 15.

Hall Sensor Package Codes

HAL XXXPA-T



Example: **HAL401SO-E**

→ Type: 401

→ Package: SOT-89A

→ Temperature Range: $T_J = -40 \text{ }^\circ\text{C}$ to $+100 \text{ }^\circ\text{C}$

Hall sensors are available in a wide variety of packaging versions and quantities. For more detailed information, please refer to the brochure: "Ordering Codes for Hall Sensors".

Solderability

– Package SOT-89A: according to IEC68-2-58

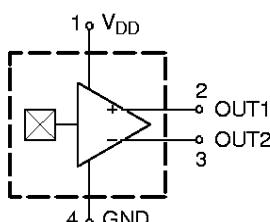


Fig. 1: Pin configuration

Functional Description

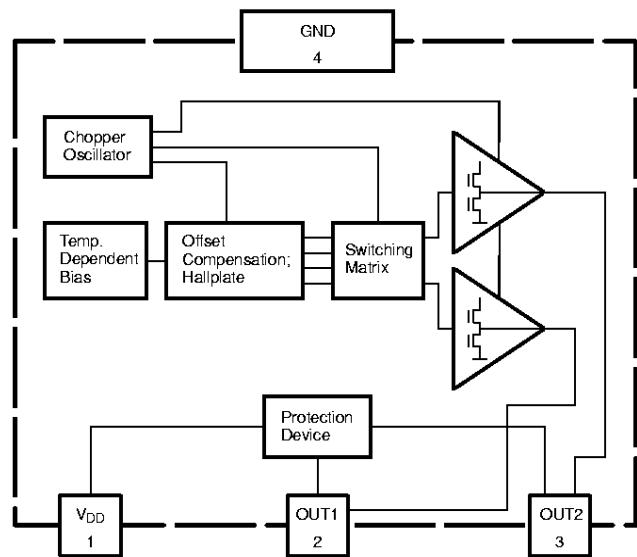


Fig. 2: Block diagram of the HAL400 (top view)

The Linear Hall Sensor measures constant and low frequency magnetic flux densities accurately. The differential output voltage V_{OUTDIF} (difference of the voltages on pin 2 and pin 3) is proportional to the magnetic flux density passing vertically through the sensitive area of the chip. The common mode voltage V_{CM} (average of the voltages on pin 2 and pin 3) of the differential output amplifier is a constant 2.2 V.

The differential output voltage consists of two components due to the switching offset compensation technique. The average of the differential output voltage represents the magnetic flux density. This component is overlaid by a differential AC signal at a typical frequency of 147 kHz. The AC signal represents the internal offset voltages of amplifiers and hall plates that are influenced by mechanical stress and temperature cycling.

External filtering or integrating measurement can be done to eliminate the AC component of the signal. Resultingly, the influence of mechanical stress and temperature cycling is suppressed. No adjustment of magnetic offset is needed.

The sensitivity is stabilized over a wide range of temperature and supply voltage due to internal voltage regulation and circuits for temperature compensation.

Offset Compensation (see Fig. 3)

The Hall Offset Voltage is the residual voltage measured in absence of a magnetic field (zero-field residual voltage). This voltage is caused by mechanical stress and can be modeled by a displacement of the connections for voltage measurement and/or current supply.

Compensation of this kind of offset is done by cyclic commutating the connections for current flow and voltage measurement.

– First cycle:

The hall supply current flows between points 4 and 2. In the absence of a magnetic field, V_{13} is the Hall Offset Voltage ($+V_{Offs}$). In case of a magnetic field, V_{13} is the sum of the Hall voltage (V_H) and V_{Offs} .

$$V_{13} = V_H + V_{Offs}$$

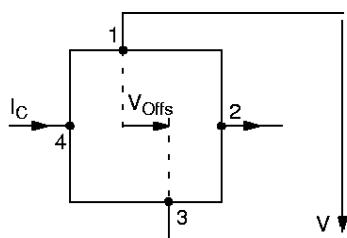
– Second cycle:

The hall supply current flows between points 1 and 3. In the absence of a magnetic field, V_{24} is the Hall Offset Voltage with negative polarity ($-V_{Offs}$). In case of a magnetic field, V_{24} is the difference of the Hall voltage (V_H) and V_{Offs} .

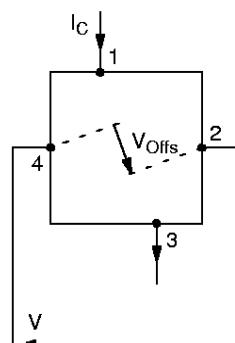
$$V_{24} = V_H - V_{Offs}$$

In the first cycle, the output shows the sum of the Hall voltage and the offset; in the second, the difference of both. The difference of the mean values of V_{OUT1} and V_{OUT2} (V_{OUTDIF}) is equivalent to V_{Hall} .

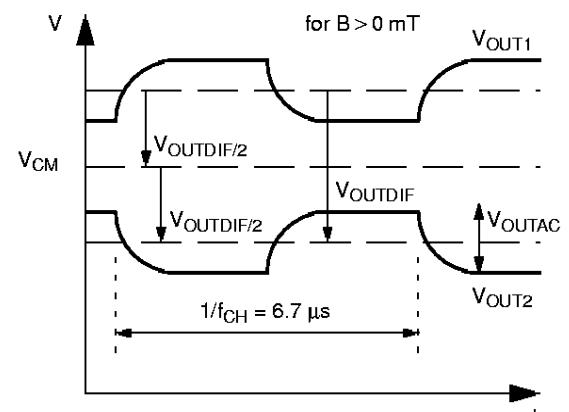
Note: The numbers do not represent pin numbers.



a) Offset Voltage

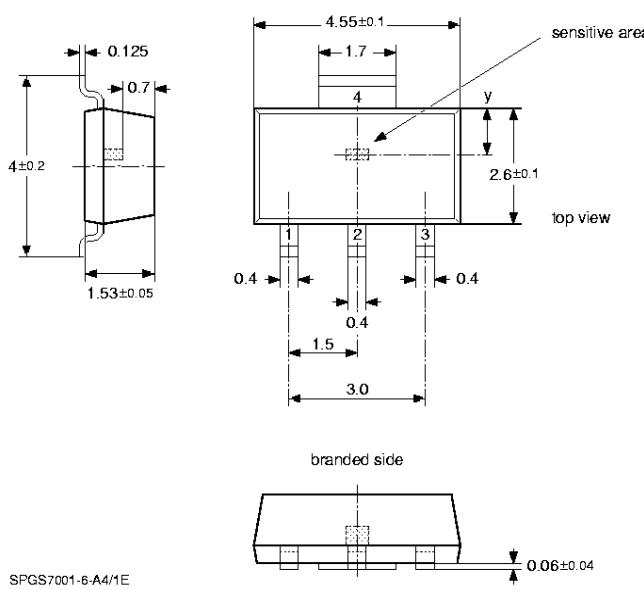


b) Switched Current Supply



c) Output Voltage

Fig. 3: Hall Offset Compensation

Outline Dimensions

SPGS7001-6-A4/1E

Dimensions of Sensitive Area

0.37 mm x 0.17 mm

Position of Sensitive Area**SOT-89A**

x = 0 ± 0.2 mm

y = 0.98 mm ± 0.2 mm

x is referenced to the center of the package

Fig. 4:
Plastic Small Outline Transistor Package
(SOT-89A)

Weight approximately 0.04 g

Dimensions in mm

Absolute Maximum Ratings

Symbol	Parameter	Pin No.	Min.	Max.	Unit
V _{DD}	Supply Voltage	1	-12	12	V
-I _{DD}	Reverse Supply Current	1	-	50 ¹⁾	mA
I _{DDZ}	Supply Current through Protection Device	1	-300 ²⁾	300 ²⁾	mA
V _O	Output Voltage	2, 3	-0.3	12	V
I _O	Continuous Output Current	2, 3	-5	5	mA
I _{Omax}	Peak Output Current	2, 3	-	50 ²⁾	mA
I _{OZ}	Output Current through Protection Device	2, 3	-200 ²⁾	200 ²⁾	mA
T _S	Storage Temperature Range		-65	150	°C
T _J	Junction Temperature Range		-40 -40	150 170 ³⁾	°C °C

¹⁾ as long as T_{Jmax} is not exceeded²⁾ t ≤ 2 ms³⁾ t < 1000 h

Stresses beyond those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only. Functional operation of the device at these or any other conditions beyond those indicated in the "Recommended Operating Conditions/Characteristics" of this specification is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Symbol	Parameter	Pin No.	Min.	Max.	Unit	Remarks
I_O	Continuous Output Current	2, 3	-2.25	2.25	mA	$T_J = 25^\circ\text{C}$
I_O	Continuous Output Current	2, 3	-1	1	mA	$T_J = 170^\circ\text{C}$
C_L	Load Capacitance	2, 3	-	1	nF	
B	Magnetic Field Range		-75	75	mT	for HAL400
B	Magnetic Field Range		-50	50	mT	for HAL401

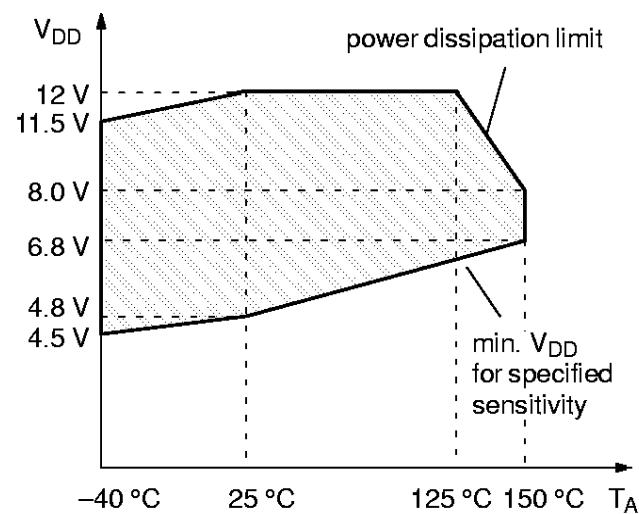


Fig. 5: Recommended Operating Supply Voltage

Electrical and Magnetic Characteristicsat Recommended Operation Conditions (Fig. 5 for T_J and V_{DD}) as not otherwise specified in the column "Conditions".Typical characteristics: $T_J = 25^\circ\text{C}$, $V_{DD} = 6.8 \text{ V}$ and $-75 \text{ mT} < B < 75 \text{ mT}$ for HAL400 $T_J = 25^\circ\text{C}$, $V_{DD} = 6.8 \text{ V}$ and $-50 \text{ mT} < B < 50 \text{ mT}$ for HAL401

Symbol	Parameter	Pin No.	Min.	Typ.	Max.	Unit	Conditions
I_{DD}	Supply Current	1	11	14.5	17.1	mA	$T_J = 25^\circ\text{C}$, $I_{OUT1,2} = 0 \text{ mA}$
I_{DD}	Supply Current over Temperature Range	1	9	14.5	18.5	mA	$I_{OUT1,2} = 0 \text{ mA}$
V_{CM}	Common Mode Output Voltage $V_{CM} = (V_{OUT1} + V_{OUT2}) / 2$	2, 3	2.1	2.2	2.3	V	$I_{OUT1,2} = 0 \text{ mA}$,
CMRR	Common Mode Rejection Ratio	2, 3	-2	0	2	mV/V	$I_{OUT1,2} = 0 \text{ mA}$, CMRR is limited by the influence of power dissipation.
S_B	Differential Magnetic Sensitivity $S_B = \Delta V_{OUTDIF}/\Delta B$ $V_{OUTDIF} = V_{OUT1} - V_{OUT2}$	2-3	37	42.5	50	mV/mT	for HAL400: $-60 \text{ mT} < B < 60 \text{ mT}$, $T_J = 25^\circ\text{C}$
S_B	Differential Magnetic Sensitivity	2-3	37	42.5	50	mV/mT	for HAL401: $-50 \text{ mT} < B < 50 \text{ mT}$, $T_J = 25^\circ\text{C}$
S_B	Differential Magnetic Sensitivity over Temperature Range	2-3	33	42.5	50	mV/mT	for HAL400: $-60 \text{ mT} < B < 60 \text{ mT}$
S_B	Differential Magnetic Sensitivity over Temperature Range	2-3	33	42.5	50	mV/mT	for HAL401: $-50 \text{ mT} < B < 50 \text{ mT}$
B_{offset}	Magnetic Offset	2-3	-1.0	-0.2	1.0	mT	for HAL400: $B = 0 \text{ mT}$, $I_{OUT1,2} = 0 \text{ mA}$, $T_J = 25^\circ\text{C}$
B_{offset}	Magnetic Offset over Temperature	2-3	-1.25	-0.2	1.25	mT	for HAL400: $B = 0 \text{ mT}$, $I_{OUT1,2} = 0 \text{ mA}$
B_{offset}	Magnetic Offset over Temperature	2-3	-1.5	-0.2	1.5	mT	for HAL401: $B = 0 \text{ mT}$, $I_{OUT1,2} = 0 \text{ mA}$
$\Delta B_{OFFSET}/\Delta T$	Magnetic Offset Change		-15	0	15	µT/K	for HAL400: $B = 0 \text{ mT}$, $I_{OUT1,2} = 0 \text{ mA}$
$\Delta B_{OFFSET}/\Delta T$	Magnetic Offset Change		-25	0	25	µT/K	for HAL401: $B = 0 \text{ mT}$, $I_{OUT1,2} = 0 \text{ mA}$
BW	Bandwidth (-3 dB)	2-3	-	10	-	kHz	without external Filter ¹⁾
NL _{dif}	Non-Linearity of Differential Output	2-3	-	0.5	1.5	%	for HAL400: $-60 \text{ mT} < B < 60 \text{ mT}$
NL _{dif}	Non-Linearity of Differential Output	2-3	-	0.5	2	%	for HAL401: $-50 \text{ mT} < B < 50 \text{ mT}$
NL _{single}	Non-Linearity of Single Ended Output	2, 3	-	2	-	%	
f _{CH}	Chopper Frequency	2, 3	110	147	170	kHz	$T_J = 25^\circ\text{C}$
f _{CH}	Chopper Frequency over Temp.	2, 3	80	147	180	kHz	
V _{OUTACpp}	Peak-to-Peak AC Output Voltage	2, 3	-	0.6	0.8	V	for HAL400
V _{OUTACpp}	Peak-to-Peak AC Output Voltage	2, 3	-	0.6	1.3	V	for HAL401
n _{meff}	Magnetic RMS Differential Broadband Noise	2-3	-	10	-	µT	BW = 10 Hz to 10 kHz

Symbol	Parameter	Pin No.	Min.	Typ.	Max.	Unit	Conditions
f_{flicker}	Corner Frequency of 1/f Noise	2–3	—	10	—	Hz	$B = 0 \text{ mT}$
f_{flicker}	Corner Frequency of 1/f Noise	2–3	—	100	—	Hz	$B = 65 \text{ mT}$
R_{OUT}	Output Impedance	2, 3	—	30	50	Ω	$I_{\text{OUT1,2}} \leq 2.5 \text{ mA}$, $T_J = 25^\circ \text{C}$, $V_{\text{DD}} = 6.8 \text{ V}$
R_{OUT}	Output Impedance over Temperature	2, 3	—	30	150	Ω	$I_{\text{OUT1,2}} \leq 2.5 \text{ mA}$
R_{ThJSB} case	Thermal Resistance Junction to Substrate Backside		—	150	200	K/W	Fiberglass Substrate 30 mm x 10 mm x 1.5 mm pad size see Fig. 29

¹⁾ with external 2 pole filter ($f_{3\text{db}} = 5 \text{ kHz}$), V_{OUTAC} is reduced to less than 1 mV by limiting the bandwidth

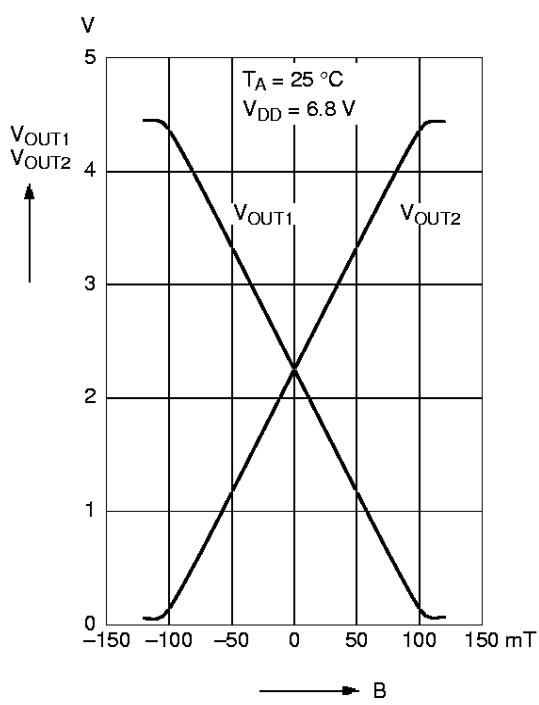


Fig. 6: Typical output voltages versus magnetic flux density

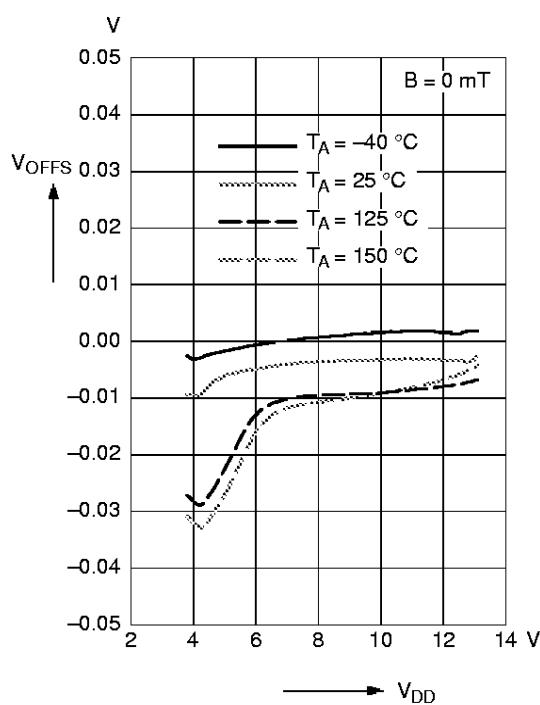


Fig. 8: Typical differential output offset voltage versus supply voltage

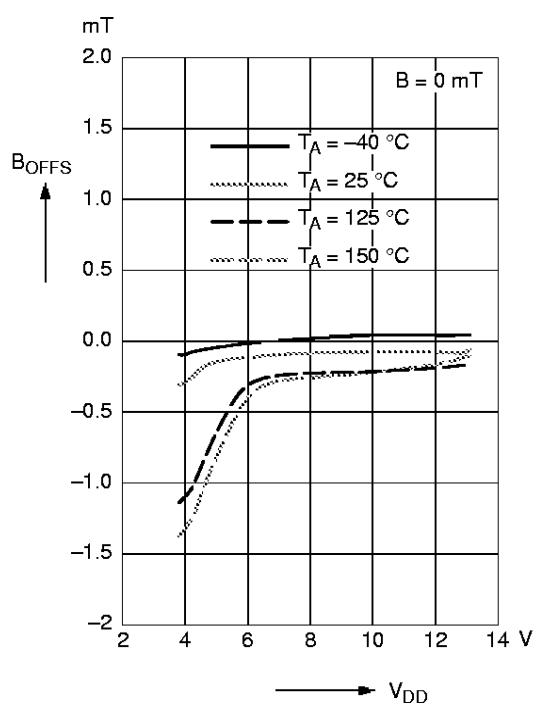


Fig. 7: Typical magnetic offset of differential output versus supply voltage

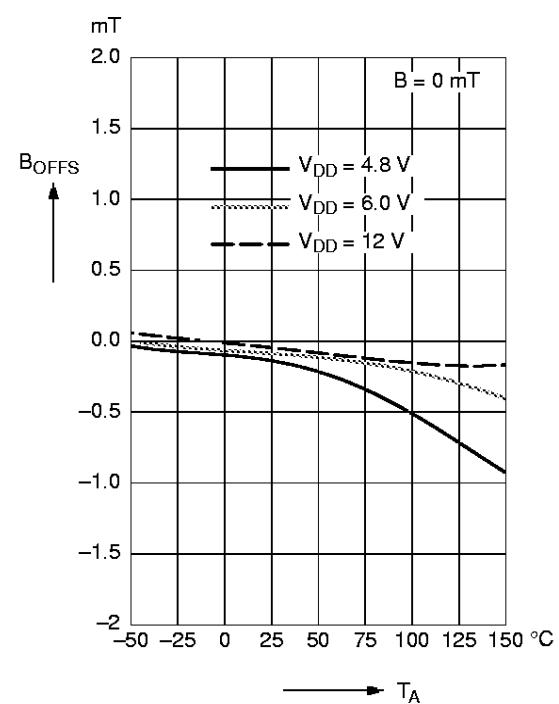


Fig. 9: Typical magnetic offset of differential output versus ambient temperature

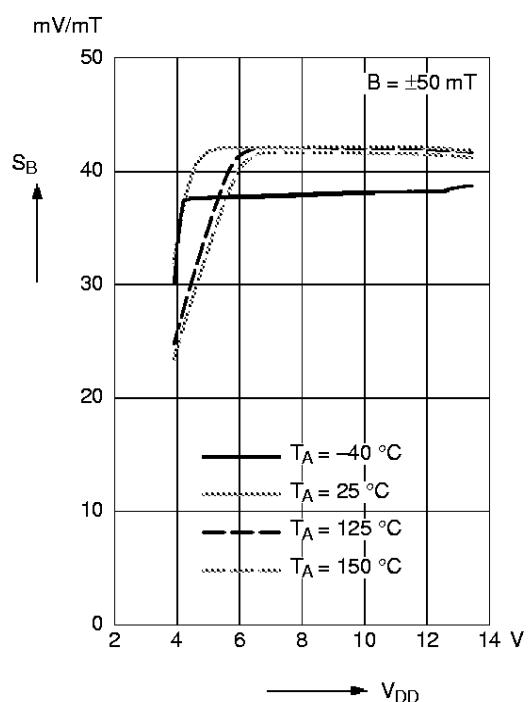


Fig. 10: Typical differential magnetic sensitivity versus supply voltage

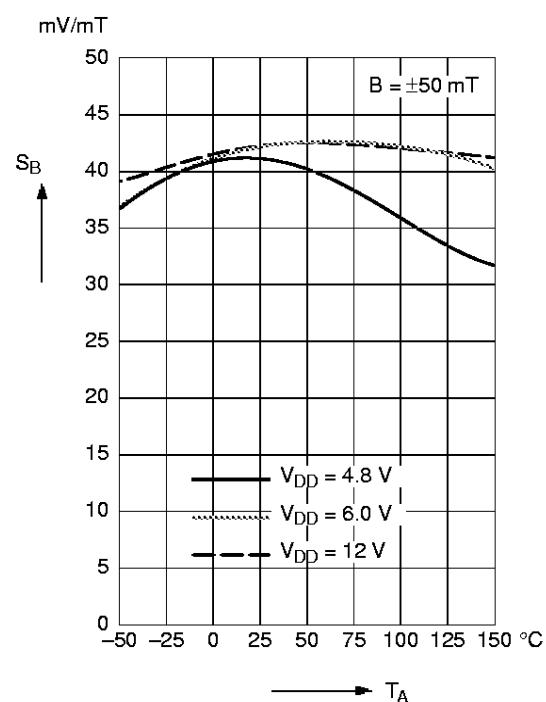


Fig. 12: Typical differential magnetic sensitivity versus ambient temperature

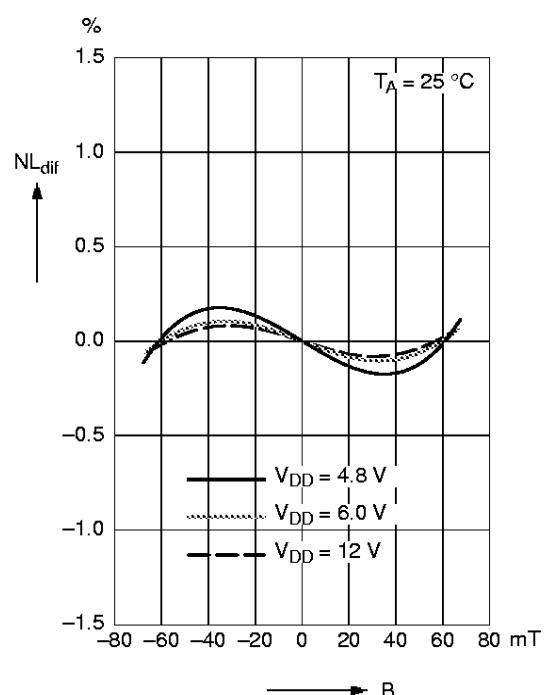


Fig. 11: Typical non-linearity of differential output versus magnetic flux density

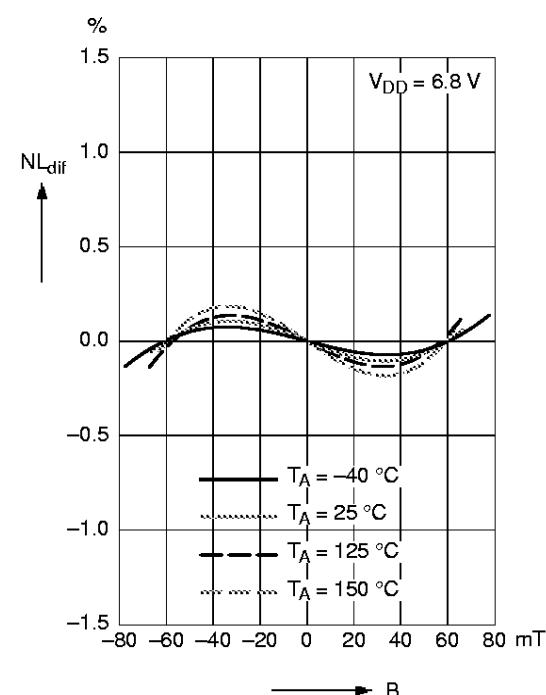


Fig. 13: Typical non-linearity of differential output versus magnetic flux density

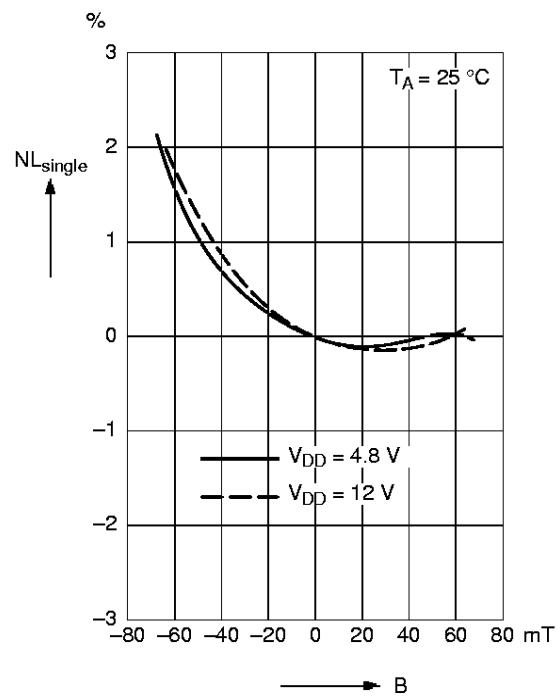


Fig. 14: Typical single-ended non-linearity versus magnetic flux density

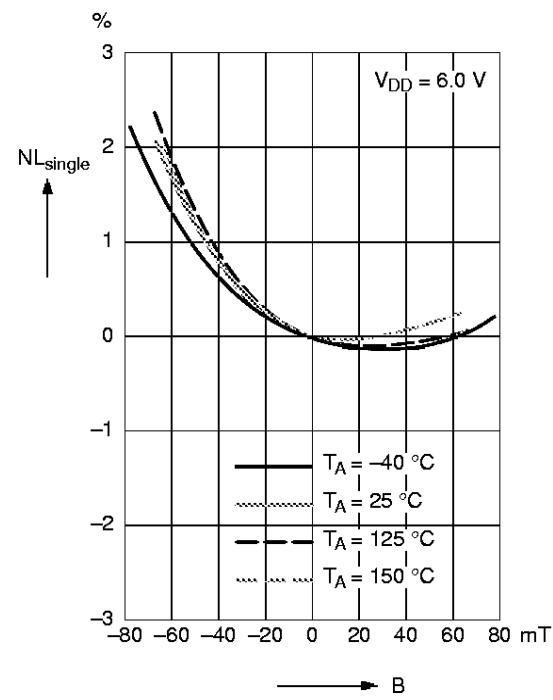


Fig. 16: Typical non-linearity of single-ended output versus magnetic flux density

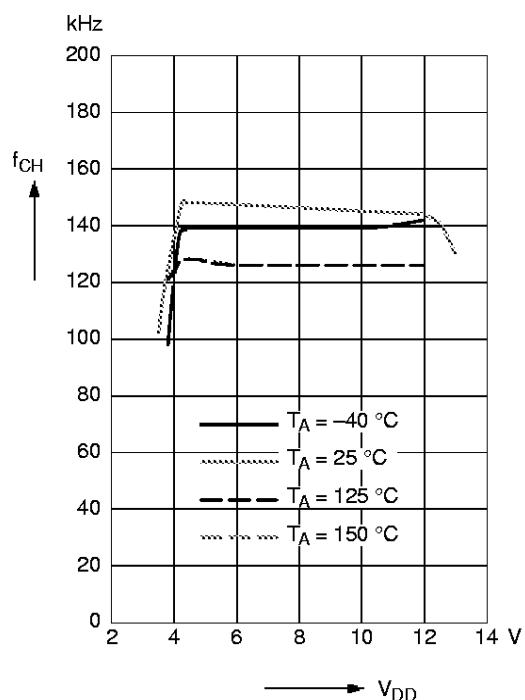


Fig. 15: Typical chopper frequency versus supply voltage

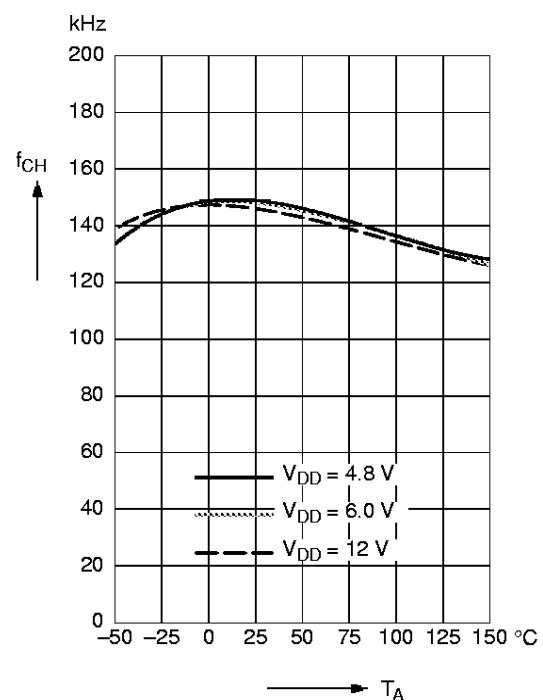


Fig. 17: Typical chopper frequency versus ambient temperature

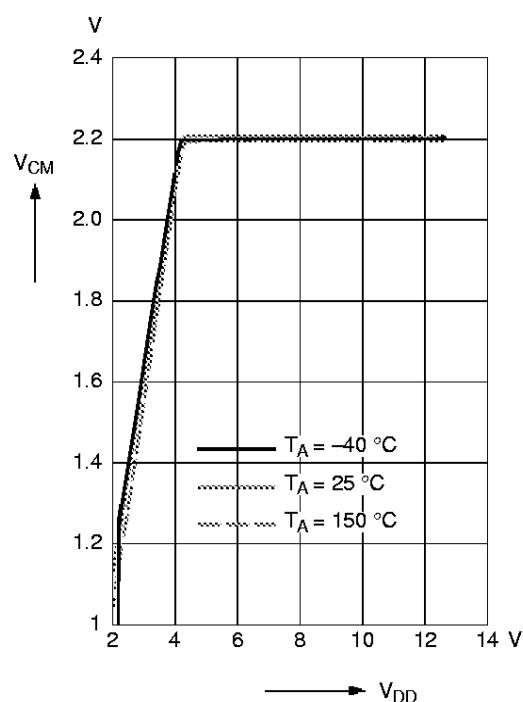


Fig. 18: Typical common mode output voltage versus supply voltage

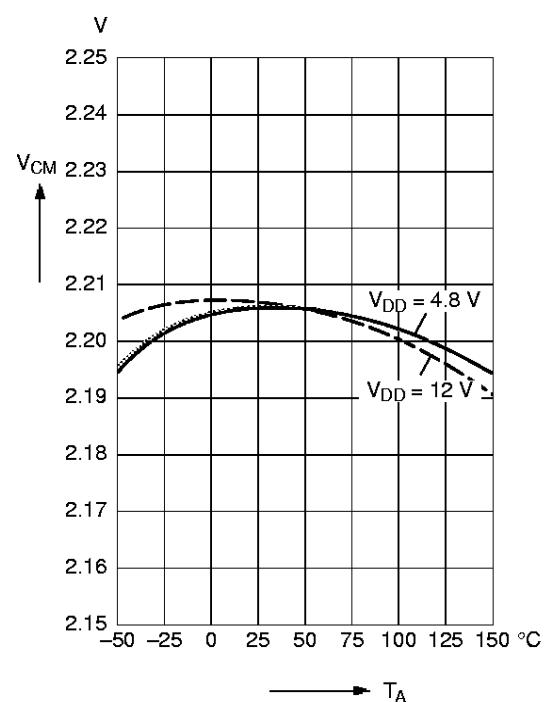


Fig. 20: Typical common mode output voltage versus ambient temperature

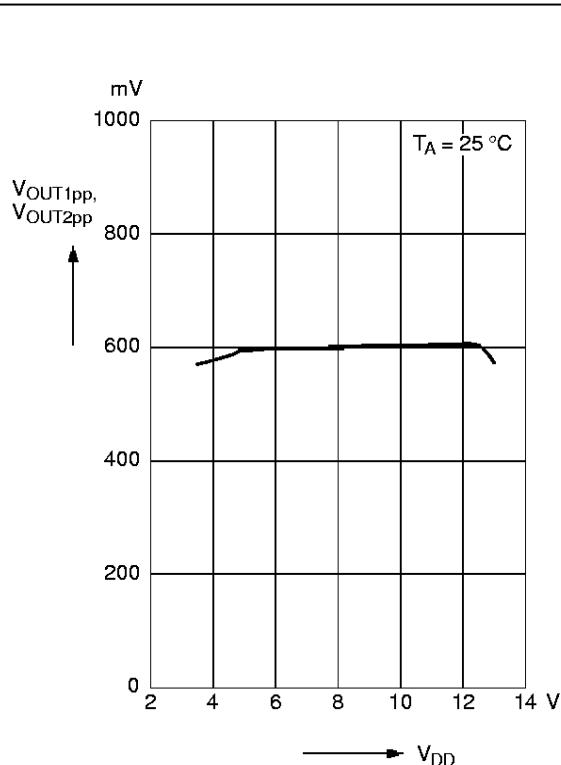


Fig. 19: Typical output AC voltage versus supply voltage

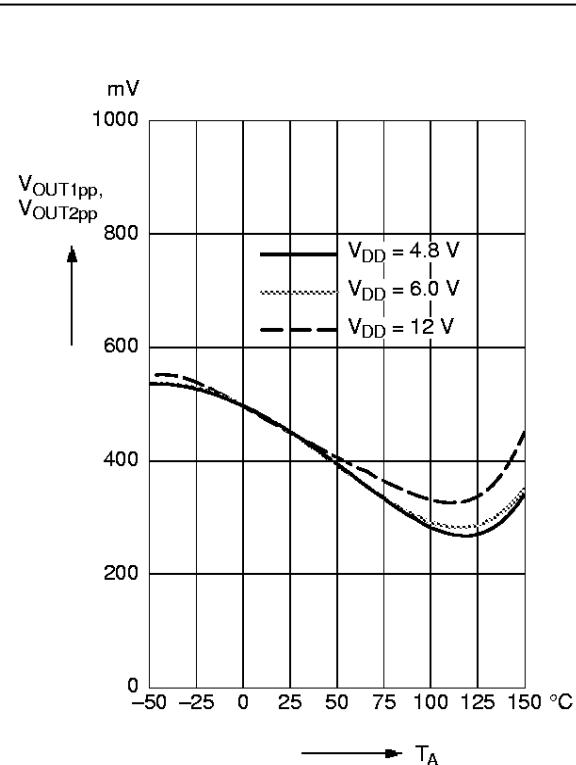


Fig. 21: Typical output AC voltage versus ambient temperature

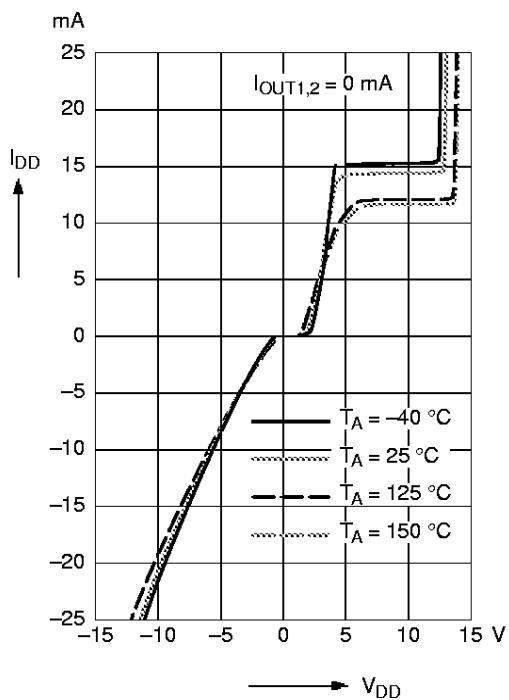


Fig. 22: Typical supply current versus supply voltage

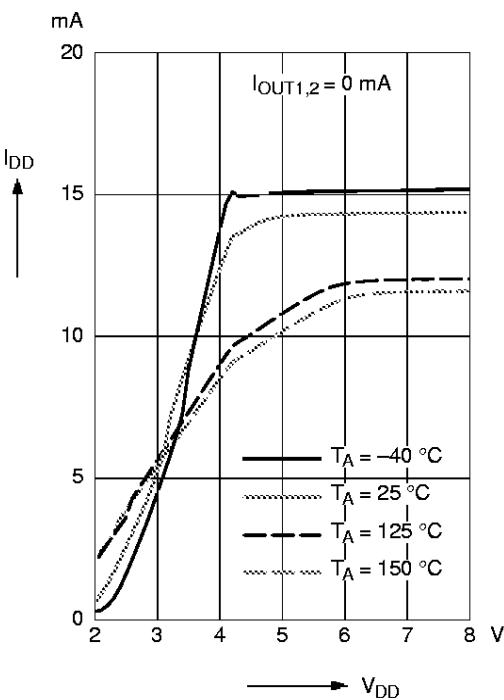


Fig. 24: Typical supply current versus supply voltage

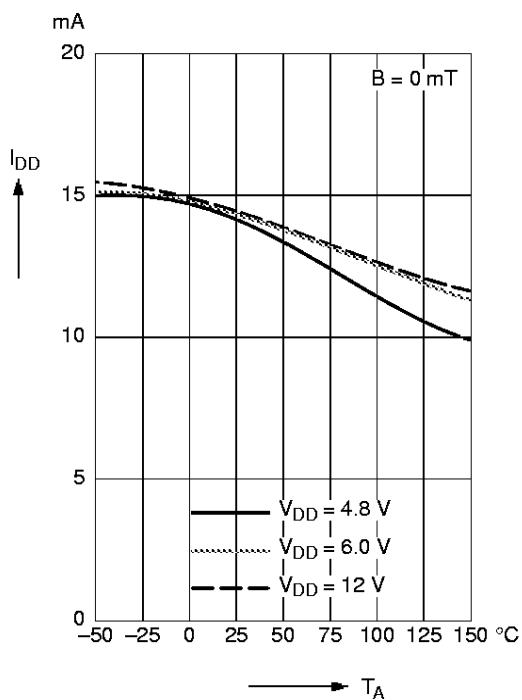


Fig. 23: Typical supply current versus temperature

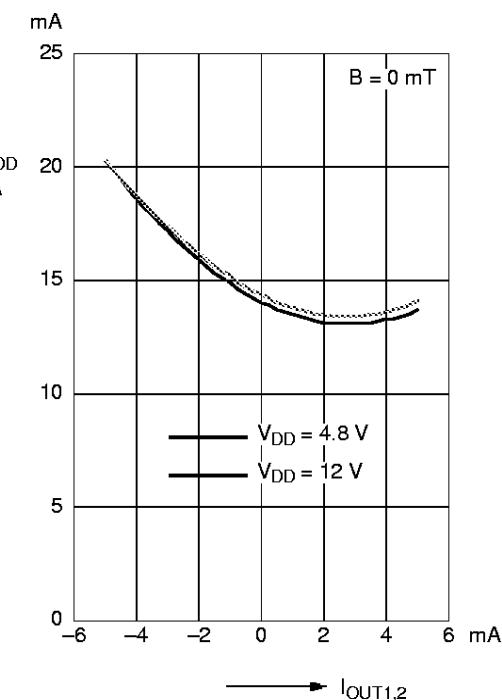


Fig. 25: Typical supply current versus output current

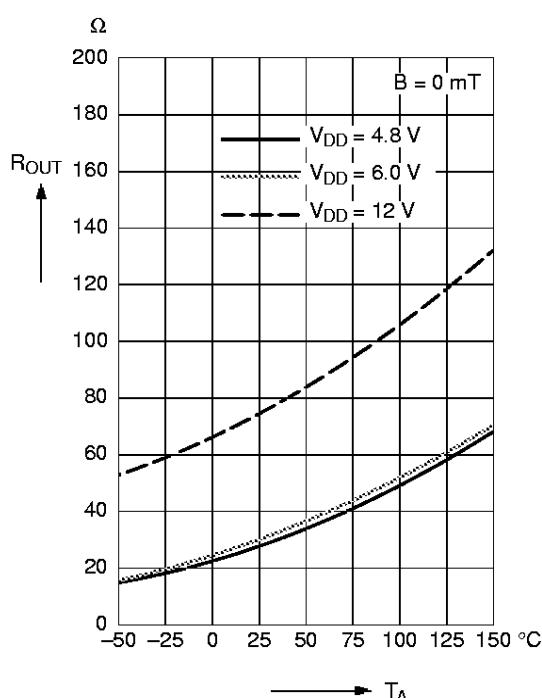


Fig. 26: Typical dynamic differential output resistance versus temperature

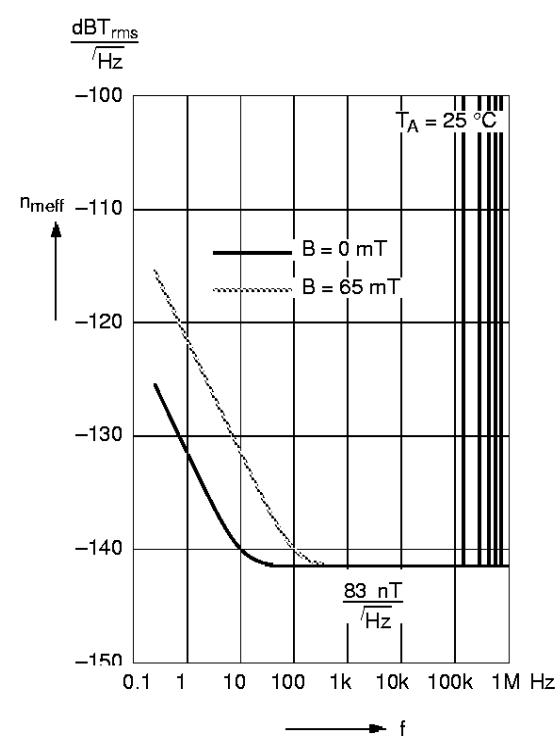


Fig. 28: Typical magnetic noise spectrum

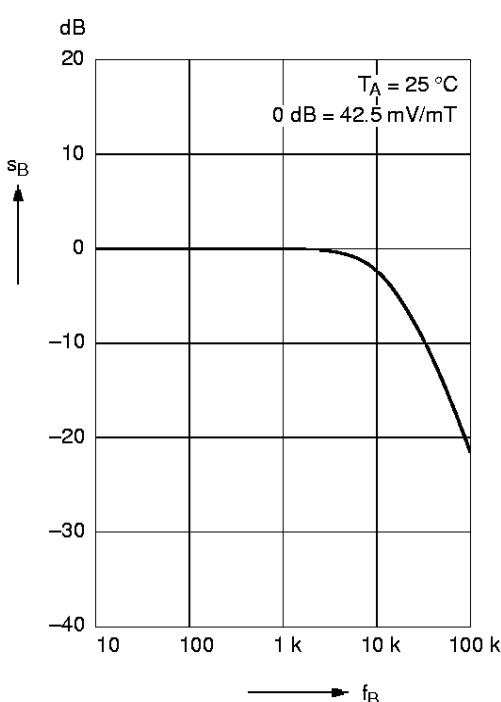


Fig. 27: Typical magnetic frequency response

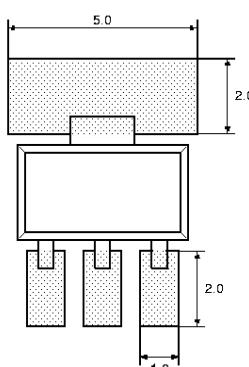


Fig. 29: Recommended pad size SOT-89A
Dimensions in mm

Application Circuits

The normal integrating characteristics of a voltmeter is sufficient for signal filtering.

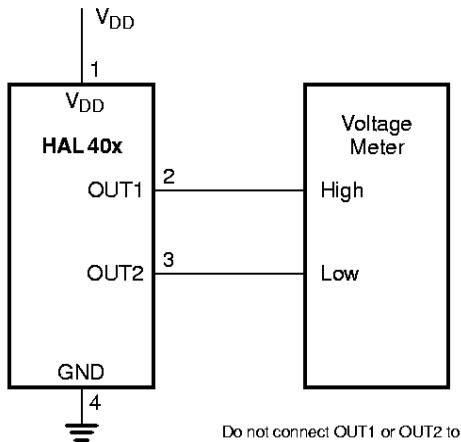


Fig. 30: Flux density measurement with voltmeter

Display the difference between channel 1 and channel 2 to show the Hall voltage. Capacitors 4.7 nF and 330 pF for electromagnetic immunity are recommended.

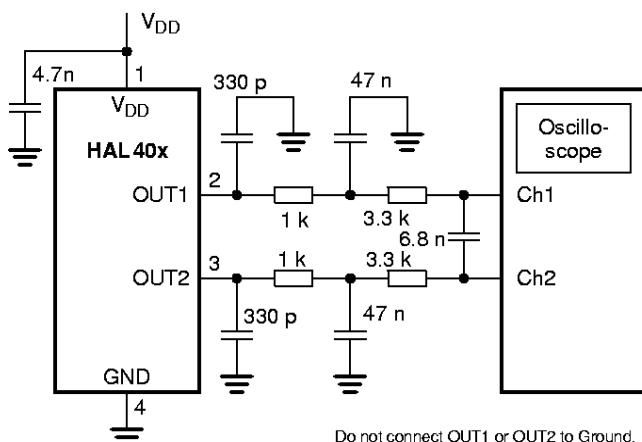


Fig. 31: Filtering of output signals

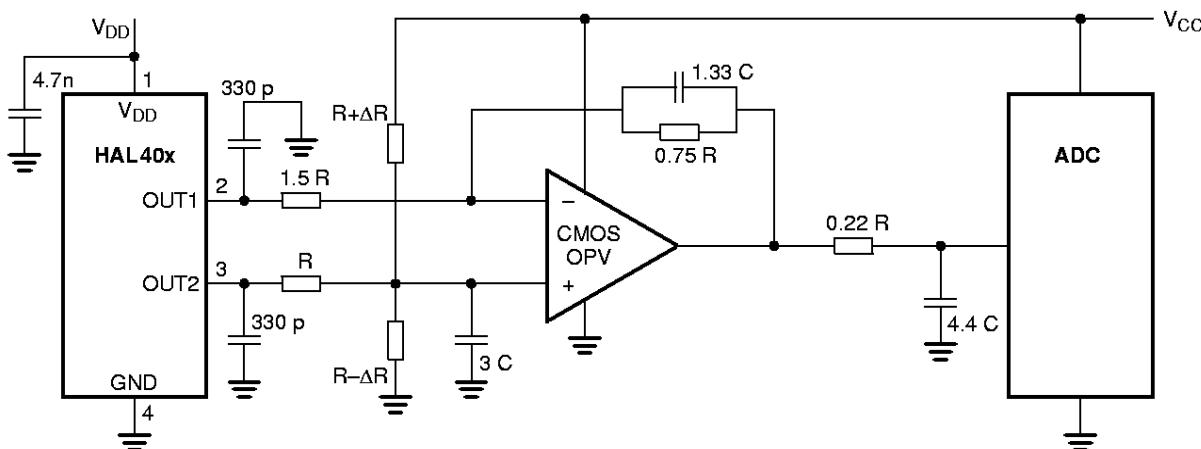


Fig. 32: Differential HAL40x output to single-ended output
 $R = 10 \text{ k}\Omega$, $C = 7.5 \text{ nF}$, ΔR for offset adjustment, $BW_{-3\text{dB}} = 1.3 \text{ kHz}$

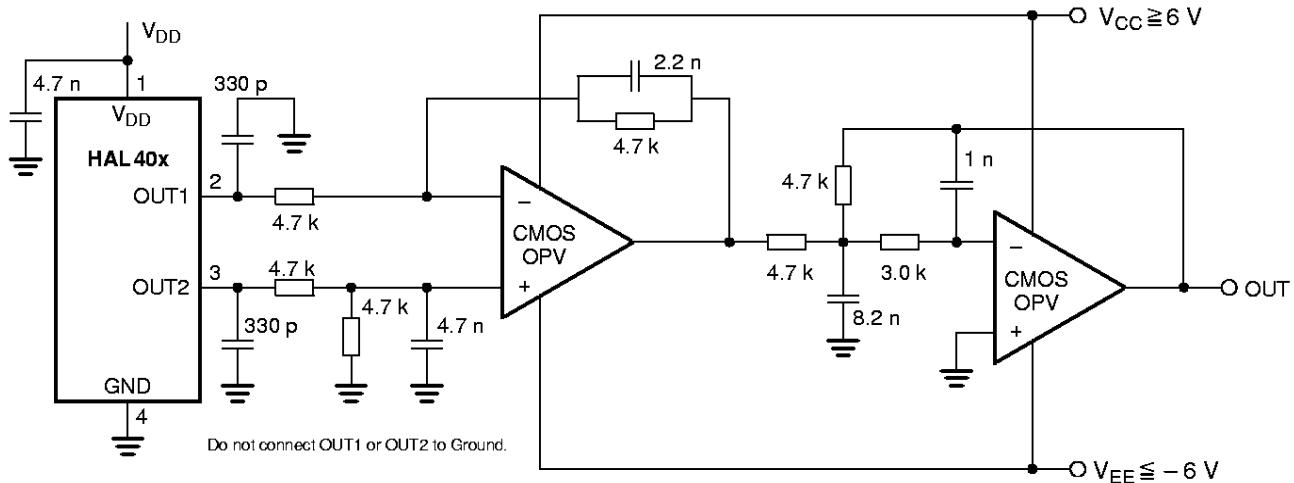


Fig. 33: Differential HAL40x output to single-ended output (referenced to ground), filter – $BW_{-3\text{dB}} = 14.7\text{ kHz}$

Ambient Temperature

Due to the internal power dissipation, the temperature on the silicon chip (junction temperature T_J) is higher than the temperature outside the package (ambient temperature T_A).

$$T_J = T_A + \Delta T$$

At static conditions, the following equations are valid:

$$\Delta T = I_{DD} * V_{DD} * R_{thJSB}$$

For typical values, use the typical parameters. For worst case calculation, use the max. parameters for I_{DD} and R_{th} , and the max. value for V_{DD} from the application.

Application Notes

Mechanical stress on the device surface (caused by the package of the sensor module or overmolding) can influence the sensor performance.

The parameter $V_{OUTACpp}$ (see Fig. 3) increases with external mechanical stress. This can cause linearity errors at the limits of the recommended operation conditions.

Data Sheet History

1. Preliminary data sheet: "HAL400 Linear Hall Effect Sensor IC", March 29, 1994, 6251-346-1PD. First release of the preliminary data sheet.

2. Preliminary data sheet: "HAL400 Linear Hall Effect Sensor IC", Aug. 1, 1995, 6251-346-2PD. Second release of the preliminary data sheet.

Major changes:

- Marking code

3. Preliminary data sheet: "HAL400 Linear Hall Effect Sensor IC", Sept. 3, 1997, 6251-346-3PD. Third release of the preliminary data sheet.

Major changes:

- Electrical and Magnetic Characteristics

- diagram: Typical output voltages versus magnetic flux density

- page 14: "Ambient Temperature"

4. Preliminary data sheet: "HAL400, HAL401 Linear Hall Effect Sensor ICs", June 29, 1998, 6251-346-4PD. Fourth release of the preliminary data sheet.

Major changes:

- additional new type HAL401

- various changes in the electrical and magnetic characteristics

- page 4: package diagram outline dimensions changed

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